IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Ritsuko Iwasaki

Serial No.: 09/496,421 Group Art Unit: 2815

Filed: February 2, 2000 Examiner: Lee, E.

5/A
12-5-01
T. Flowers

For: SEMICONDUCTOR DEVICE HAVING AN IMPROVED LAYOUT PATTERN OF PAIR TRANSISTORS

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated August 29, 2001, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please amend paragraph beginning at page 7, line 26 as follows:

Since the arrangement of the transistor 3A is substantially to that of the transistor 3B, the explanation of source and drain diffusion region 7, 8 and source and drain electrodes 17, 18 is omitted.

IN THE CLAIMS:

Please cancel claims 1, 2, and 10 without prejudice or disclaimer.

3. (~~Amended~~) A semiconductor device, comprising:

a first transistor ~~having~~ a first gate put between a first source and a first drain;

a second transistor arranged adjacent to said first transistor, said second transistor having a second gate put between a second source and a second drain;

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